

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1-73. (Cancelled)

74. (Currently Amended) A haze free PZT film prepared in accordance with the method comprising:

forming a front-end structure over a semiconductor substrate;

forming a bottom electrode over said front-end structure;

preheating said semiconductor wafer; and

forming a PZT film over said bottom electrode;

wherein said preheating step comprises placing said semiconductor wafer on a heater, and heating said semiconductor wafer in an ambient comprised of a mixture of an inert gas and an oxidizer gas.

75. (Currently Amended) A haze free PZT film prepared in accordance with the method comprising:

forming a front-end structure over a semiconductor substrate;

forming a bottom electrode over said front-end structure;

preheating said semiconductor wafer; and

forming a PZT film over said bottom electrode;

wherein said preheating step comprises placing said semiconductor wafer on a heater, and heating said semiconductor wafer in an inert gas.

76. (Currently Amended) A haze free PZT film prepared in accordance with the method comprising:

forming a front-end structure;

forming a bottom electrode over said front-end structure;

preheating said semiconductor wafer; and

forming a PZT film over said bottom electrode;

wherein said preheating step comprises placing said semiconductor wafer on a heater, and heating said semiconductor wafer in a vacuum.

77-79. (Cancelled)

80. (Original) The haze free PZT film of Claim 74 wherein said inert gas is Ar.

81. (Original) The haze free PZT film of Claim 74 wherein said inert gas is N₂.

82. (Original) The haze free PZT film of Claim 74 wherein said oxidizer gas is O₂.

83. (Original) The haze free PZT film of Claim 80, wherein Ar comprises at least 20% of the flow of said inert/oxidizer gas mixture.

84. (Original) The haze free PZT film of Claim 74 wherein said PZT film contains at least 2% excess Pb from the stoichiometric composition of $\text{Pb}_{1.0}(\text{Zr}, \text{Ti})_{1.0}\text{O}_3$.

85.(Original) The haze free PZT film of Claim 74 wherein said PZT film is a solid solution of the component end members PbZrO_3 and PbTiO_3 .

86.(Original) The haze free PZT film of Claim 74 wherein said PZT film is doped up to 5% with either La or Nb.

87.(Original) The haze free PZT film of Claim 75 wherein said inert gas is Ar.

88. (Original) The haze free PZT film of Claim 75 wherein said inert gas is N_2 .

89.(Original) The haze free PZT film of Claim 75 wherein said inert gas is He.

90.(Original) The haze free PZT film of Claim 75 wherein said PZT film contains at least 2% excess Pb from the stoichiometric composition of $\text{Pb}_{1.0}(\text{Zr,Ti})_{1.0}\text{O}_3$.

91.(Original) The haze free PZT film of Claim 75 wherein said PZT film is a solid solution of the component end members PbZrO_3 and PbTiO_3 .

92.(Original) The haze free PZT film of Claim 75 wherein said PZT film is doped up to 5% with either La or Nb.

93.(Original) The haze free PZT film of Claim 75 wherein said PZT film is PbZrO_3 .

94.(Original) The haze free PZT film of Claim 76 wherein said PZT film contains at least 2% excess Pb from the stoichiometric composition of $\text{Pb}_{1.0}(\text{Zr,Ti})_{1.0}\text{O}_3$.

95.(Original) The haze free PZT film of Claim 76 wherein said PZT film is a solid solution of the component end members PbZrO_3 and PbTiO_3 .

96.(Original) The haze free PZT film of Claim 76 wherein said PZT film is doped up to 5% with either La or Nb.

97.(Original) The haze free PZT film of Claim 76 wherein said PZT film
is PbZrO_3 .